

N-Channel Enhancement Mode Power MOSFET

Description

The RM6003S2 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other switching application.

General Features

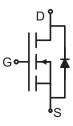
V_{DS} =60V,I_D =3A

 $R_{DS(ON)}$ <105m Ω @ V_{GS} =10V $R_{DS(ON)}$ < 125m Ω @ V_{GS} =4.5V

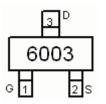
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Battery switch
- ●DC/DC converter



Schematic Diagram



Marking and Pin Assignment



SOT-23 -3L Top View

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
6003	RM6003S2	SOT-23-3L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	60	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	3	Α
Drain Current-Pulsed (Note 1)	I _{DM}	10	Α
Maximum Power Dissipation	P _D	1.7	W
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{eJA}	73.5	°C/W
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Electrical Characteristics (T_A=25 [°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	65	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA

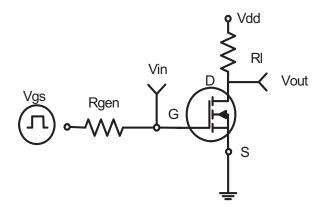
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20 V, V_{DS} = 0 V$		-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.0	1.2	1.9	V	
Drain-Source On-State Resistance	Б	V _{GS} =10V, I _D =3A	-	78	105	mΩ	
Drain-Source On-State Resistance	$R_{DS(ON)}$	V _{GS} =4.5V, I _D =3A	-	95	125	mΩ	
Forward Transconductance	g FS	V _{DS} =15V,I _D =2A		-	-	S	
Dynamic Characteristics (Note4)			•				
Input Capacitance	C _{lss}	V _{DS} =30V,V _{GS} =0V,	-	247	-	PF	
Output Capacitance	Coss	F=1.0MHz	-	34	-	PF	
Reverse Transfer Capacitance	C _{rss}	F-1.0WHZ	-	19.5	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	6	1	nS	
Turn-on Rise Time	t _r	V_{DD} =30 V , I_{D} =1.5 A	-	15	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =1 Ω	-	15	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Qg	\/ -20\/ -24	-	6	-	nC	
Gate-Source Charge	Q_{gs}	$V_{DS}=30V,I_{D}=3A,$ $V_{GS}=4.5V$	-	1	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} -4.5V	-	1.3	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =3A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	3	Α	
	_			L		l .	

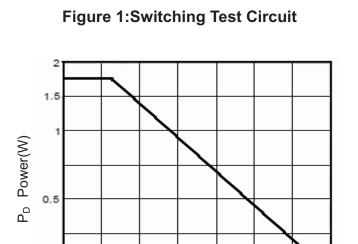
Notes:

- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, t ≤ 10 sec.
 Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



RATING AND CHARACTERISTICS CURVES (RM6003S2)





60 T_J-Junction Temperature(°C)

40

20

0

0

Figure 3 Power Dissipation

80

100

120

140

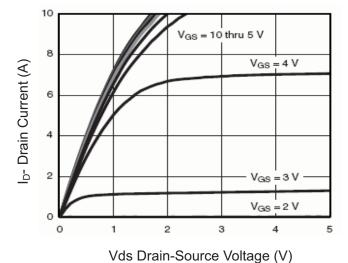


Figure 5 Output Characteristics

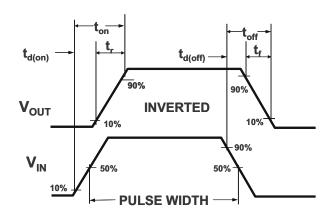


Figure 2:Switching Waveforms

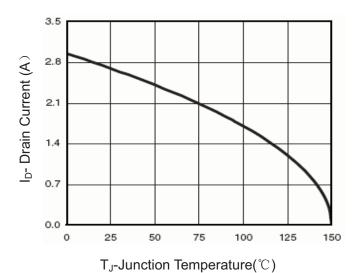


Figure 4 Drain Current

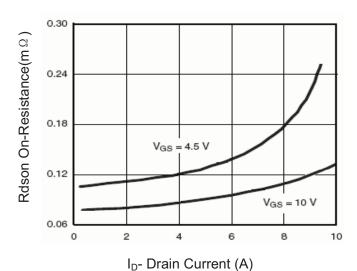
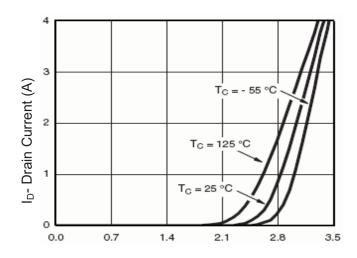


Figure 6 Drain-Source On-Resistance

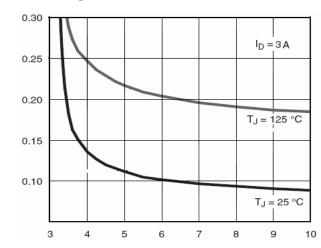


RATING AND CHARACTERISTICS CURVES (RM6003S2)



Vgs Gate-Source Voltage (V)





Rdson On-Resistance(m 2)

Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

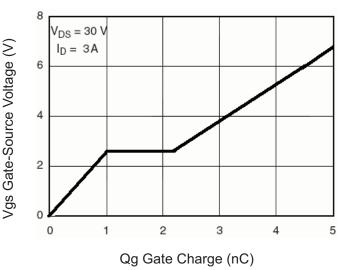
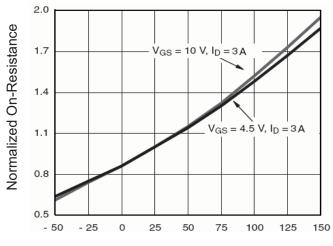
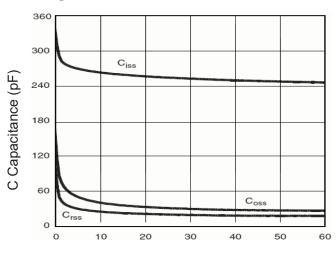


Figure 11 Gate Charge



 T_J -Junction Temperature($^{\circ}$ C)

Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

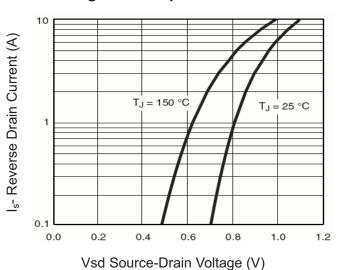


Figure 12 Source- Drain Diode Forward

RATING AND CHARACTERISTICS CURVES (RM6003S2)

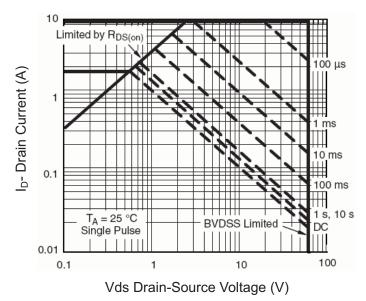


Figure 13 Safe Operation Area

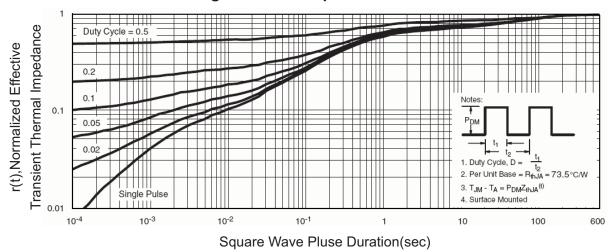
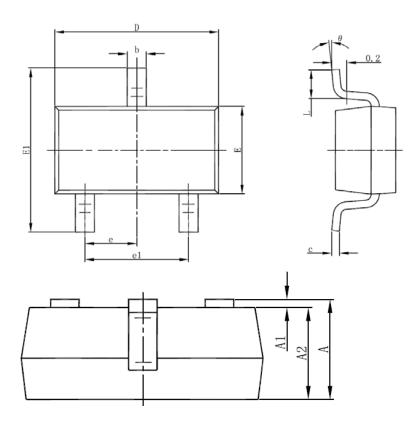


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23-3L Package Information



Country of	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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